

Atomic Layer Deposition (ALD)

Manufacturing of material layers with the accuracy of a single atomic layer

Beneq TFS 200 ALD

- Integrated to nitrogen filled glove box
 - Processing and measurement of samples without oxygen and humidity exposure
- Sample max $\varnothing = 200$ mm
- Thermal and plasma growth
- Relatively low temperature process
- Current setup designed for oxides of Al, Ti, Zn, Hf and Ta, other materials possible
- Thin film transistor and diode materials
- Barrier layers

